

August 1994

Monolithic Quad SPST CMOS Analog Switches

Features

- This Circuit is Processed in Accordance to MIL-STD-883 and is Fully Conformant Under the Provisions of Paragraph 1.2.1.
- ON-Resistance $<35\Omega$ Max
- Low Power Consumption ($P_D <35\mu W$)
- Fast Switching Action
 - $t_{ON} <175ns$
 - $t_{OFF} <145ns$
- Low Charge Injection
- Upgrade from DG211/DG212
- TTL, CMOS Compatible
- Single or Split Supply Operation

Applications

- Audio Switching
- Battery Operated Systems
- Data Acquisition
- Hi-Rel Systems
- Sample and Hold Circuits
- Communication Systems
- Automatic Test Equipment

Description

The DG411/883 series monolithic CMOS analog switches are drop-in replacements for the popular DG211 and DG212 series devices. They include four independent single pole throw (SPST) analog switches, and TTL and CMOS compatible digital inputs.

These switches feature lower analog ON resistance ($<35\Omega$) and faster switch time ($t_{ON} <175ns$) compared to the DG211 or DG212. Charge injection has been reduced, simplifying sample and hold applications.

The improvements in the DG411/883 series are made possible by using a high voltage silicon-gate process. An epitaxial layer prevents the latch-up associated with older CMOS technologies. The 44V maximum voltage range permits controlling 40V_{P-P} signals. Power supplies may be single-ended from +5V to +34V, or split from $\pm 5V$ to $\pm 20V$.

The four switches are bilateral, equally matched for AC or bidirectional signals. The ON resistance variation with analog signals is quite low over a $\pm 15V$ analog input range. The switches in the DG411/883 and DG412/883 are identical, differing only in the polarity of the selection logic. Two of the switches in the DG413/883 (#1 and #4) use the logic of the DG211 and DG411/883 (i.e. a logic "0" turns the switch ON) and the other two switches use DG212 and DG412/883 positive logic. This permits independent control of turn-on and turn-off times for SPDT configurations, permitting "break-before-make" or "make-before-break" operation with a minimum of external logic.

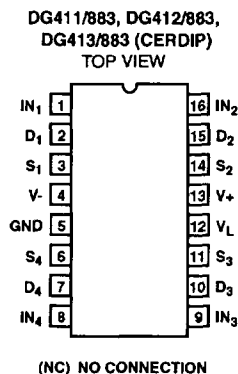
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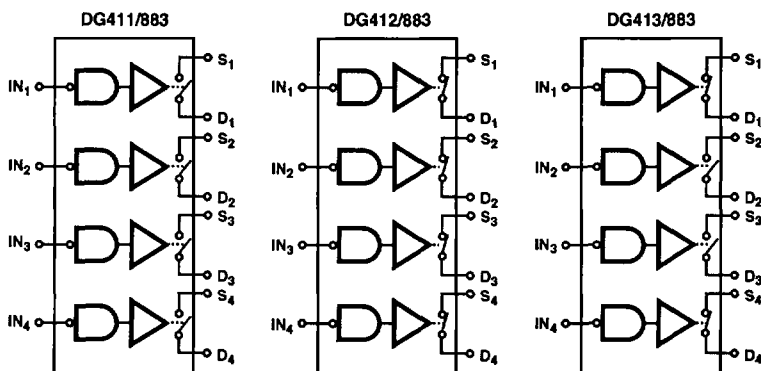
Ordering Information

PART NUMBER	TEMP. RANGE	PACKAGE
DG411AK/883	-55°C to +125°C	16 Lead CerDIP
DG412AK/883	-55°C to +125°C	16 Lead CerDIP
DG413AK/883	-55°C to +125°C	16 Lead CerDIP

Pinout



Functional Diagrams



Pin Description

PIN	SYMBOL	DESCRIPTION
1	IN ₁	Logic Control for Switch 1
2	D ₁	Drain (Output) Terminal for Switch 1
3	S ₁	Source (Input) Terminal for Switch 1
4	V-	Negative Power Supply Terminal
5	GND	Ground Terminal (Logic Common)
6	S ₄	Source (Input) Terminal for Switch 4
7	D ₄	Drain (Output) Terminal for Switch 4
8	IN ₄	Logic Control for Switch 4
9	IN ₃	Logic Control for Switch 3
10	D ₃	Drain (Output) Terminal for Switch 3
11	S ₃	Source (Input) Terminal for Switch 3
12	V _L	Logic Reference Voltage
13	V+	Positive Power Supply Terminal (Substrate)
14	S ₂	Source (Input) Terminal for Switch 2
15	D ₂	Drain (Output) Terminal for Switch 2
16	IN ₂	Logic Control for Switch 2

TRUTH TABLE

LOGIC	DG411/ 883	DG412/ 883	DG413/883	
	SWITCH	SWITCH	SWITCH 1, 4	SWITCH 2, 3
0	ON	OFF	OFF	ON
1	OFF	ON	ON	OFF

NOTE: Logic "0" ≤0.8V. Logic "1" ≥2.4V.

Specifications DG411/883, DG412/883, DG413/883

Absolute Maximum Ratings

V₊ to V₋ 44V
 GND to V₋ 25V
 V_L (Note 2) (GND -0.3V) to (V₊) +0.3V
 Digital Inputs, V_S, V_D (Note 2) (V₋) -2V to (V₊) + 2V or 30mA,
 Whichever Occurs First
 Continuous Current (Any Terminal) 30mA
 Current, S or D (Pulsed 1ms, 10% Duty Cycle) 100mA
 Storage Temperature Range (A Suffix) -65°C to +125°C
 Lead Temperature (Soldering 10s) +300°C

Thermal Information

Thermal Resistance (Note 3)
 CerDIP Package θ_{JA} 85°C/W θ_{JC} 24°C/W
 Junction Temperature +175°C
 Operating Temperature (A Suffix) -55°C to +125°C

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

Operating Conditions

Operating Voltage Range ±20V Max Input High Voltage 2.4V Min
 Operating Temperature Range -55°C to +125°C Input Rise and Fall Time ≤20ns
 Input Low Voltage 0.8V Max

TABLE 1. DC ELECTRICAL PERFORMANCE CHARACTERISTICS

Device Tested at: V₊ = +15V, V₋ = -15V, V_L = 5V, GND = 0V, Unless Otherwise Specified

PARAMETERS	SYMBOL	CONDITIONS		GROUP A SUBGROUP	TEMPERATURE	LIMITS		UNITS			
						MIN	MAX				
Drain-to-Source ON Resistance DG411/883	R _{DS(ON)}	V ₊ = +13.5V, V ₋ = -13.5V, I _S = -10mA, V _D = ±8.5V	V _{IN} = 0.8V	1, 3	+25°C, -55°C	0	35	Ω			
DG412/883			V _{IN} = 2.4V	2	+125°C	0	45	Ω			
DG413/883				1, 3	+25°C, -55°C	0	35	Ω			
			DG411/883	2	+125°C	0	45	Ω			
DG412/883				V _{IN} = 0.8V or 2.4V (Note 1)	1, 3	+25°C, -55°C	0	35	Ω		
			DG413/883	2	+125°C	0	45	Ω			
Source OFF Leakage Current DG411/883	I _{S(OFF)}	V ₊ = +10.8V, V ₋ = -0V, I _S = -10mA, V _D = 3.0V and 8.0V	V _{IN} = 0.8V	1, 3	+25°C, -55°C	0	80	Ω			
			V _{IN} = 2.4V	2	+125°C	0	100	Ω			
				V _{IN} = 0.8V or 2.4V (Note 1)	1, 3	+25°C, -55°C	0	80	Ω		
			DG412/883		2	+125°C	0	100	Ω		
			DG413/883	V _{IN} = 0.8V or 2.4V (Note 1)	1, 3	+25°C, -55°C	0	80	Ω		
				2	+125°C	0	100	Ω			
Source OFF Leakage Current DG411/883			I _{S(OFF)}	V ₊ = 16.5V, V ₋ = -16.5V, V _D = -15.5V, V _S = 15.5V	V _{IN} = 2.4V	1	+25°C	-0.25	+0.25	nA	
					V _{IN} = 0.8V	2, 3	+125°C, -55°C	-20	+20	nA	
						V _{IN} = 0.8V or 2.4V (Note 1)	1	+25°C	-0.25	+0.25	nA
					DG412/883		2, 3	+125°C, -55°C	-20	+20	nA
					DG413/883	V _{IN} = 2.4V	1	+25°C	-0.25	+0.25	nA
						V _{IN} = 0.8V	2, 3	+125°C, -55°C	-20	+20	nA
	DG411/883	V _{IN} = 0.8V or 2.4V (Note 1)			1		+25°C	-0.25	+0.25	nA	
		DG412/883			2, 3	+125°C, -55°C	-20	+20	nA		
	DG413/883	V _{IN} = 0.8V or 2.4V (Note 1)			1	+25°C	-0.25	+0.25	nA		
		2, 3			+125°C, -55°C	-20	+20	nA			

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Specifications DG411/883, DG412/883, DG413/883

TABLE 1. DC ELECTRICAL PERFORMANCE CHARACTERISTICS (Continued)

Device Tested at: $V_+ = +15V$, $V_- = -15V$, $V_L = 5V$, $GND = 0V$, Unless Otherwise Specified

PARAMETERS	SYMBOL	CONDITIONS		GROUP A SUBGROUP	TEMPERATURE	LIMITS		UNITS
						MIN	MAX	
Drain OFF Leakage Current	$I_{D(OFF)}$	$V_+ = 16.5V$, $V_- = -16.5V$, $V_D = -15.5V$, $V_S = 15.5V$	$V_{IN} = 2.4V$	1	+25°C	-0.25	+0.25	nA
DG411/883				2, 3	+125°C, -55°C	-20	+20	nA
DG412/883			$V_{IN} = 0.8V$	1	+25°C	-0.25	+0.25	nA
				2, 3	+125°C, -55°C	-20	+20	nA
DG413/883			$V_{IN} = 0.8V$ or 2.4V (Note 1)	1	+25°C	-0.25	+0.25	nA
				2, 3	+125°C, -55°C	-20	+20	nA
DG411/883		$V_+ = 16.5V$, $V_- = -16.5V$, $V_D = 15.5V$, $V_S = -15.5V$	$V_{IN} = 2.4V$	1	+25°C	-0.25	+0.25	nA
				2, 3	+125°C, -55°C	-20	+20	nA
DG412/883			$V_{IN} = 0.8V$	1	+25°C	-0.25	+0.25	nA
				2, 3	+125°C, -55°C	-20	+20	nA
DG413/883			$V_{IN} = 0.8V$ or 2.4V (Note 1)	1	+25°C	-0.25	+0.25	nA
				2, 3	+125°C, -55°C	-20	+20	nA
Channel ON Leakage Current	$I_{D(ON)} + I_{S(ON)}$	$V_+ = 16.5V$, $V_- = -16.5V$, $V_S = V_D = \pm 15.5V$	$V_{IN} = 0.8V$	1	+25°C	-0.4	+0.4	nA
DG411/883				2, 3	+125°C, -55°C	-40	+40	nA
DG412/883			$V_{IN} = 2.4V$	1	+25°C	-0.4	+0.4	nA
				2, 3	+125°C, -55°C	-40	+40	nA
DG413/883			$V_{IN} = 0.8V$ or 2.4V (Note 1)	1	+25°C	-0.4	+0.4	nA
				2, 3	+125°C, -55°C	-40	+40	nA
Input Current with V_{IN} Low	I_{IL}	Input Under Test = 0.8V, All Others = 2.4V	1, 2, 3	+25°C, +125°C, -55°C	-0.5	+0.5	μA	
Input Current with V_{IN} High	I_{IH}	Input Under Test = 2.4V, All Others = 0.8V	1, 2, 3	+25°C, +125°C, -55°C	-0.5	+0.5	μA	
Positive Supply Current	I_+	$V_+ = 16.5V$, $V_- = -16.5V$, $V_{IN} = 0V$ or 5.0V	1	+25°C	-	+1.0	μA	
			2, 3	+125°C, -55°C	-	+5.0	μA	
		$V_+ = 13.2V$, $V_- = 0V$, $V_{IN} = 0V$ or 5.0V $V_L = 5.25V$	1	+25°C	-	+1.0	μA	
			2, 3	+125°C, -55°C	-	+5.0	μA	
Negative Supply Current	I_-	$V_+ = 16.5V$, $V_- = -16.5V$, $V_{IN} = 0V$ or 5.0V	1	+25°C	-1.0	-	μA	
			2, 3	+125°C, -55°C	-5.0	-	μA	
		$V_+ = 13.2V$, $V_- = 0V$, $V_{IN} = 0V$ or 5.0V $V_L = 5.25V$	1	+25°C	-1.0	-	μA	
			2, 3	+125°C, -55°C	-5.0	-	μA	
Logic Supply Current	I_L	$V_+ = 16.5V$, $V_- = -16.5V$, $V_{IN} = 0V$ or 5.0V	1	+25°C	-	+1.0	μA	
			2, 3	+125°C, -55°C	-	+5.0	μA	
		$V_+ = 13.2V$, $V_- = 0V$, $V_{IN} = 0V$ or 5.0V $V_L = 5.25V$	1	+25°C	-	+1.0	μA	
			2, 3	+125°C, -55°C	-	+5.0	μA	
Ground Current	I_{GND}	$V_+ = 16.5V$, $V_- = -16.5V$, $V_{IN} = 0V$ or 5.0V	1	+25°C	-1.0	-	μA	
			2, 3	+125°C, -55°C	-5.0	-	μA	
		$V_+ = 13.2V$, $V_- = 0V$, $V_{IN} = 0V$ or 5.0V $V_L = 5.25V$	1	+25°C	-1.0	-	μA	
			2, 3	+125°C, -55°C	-5.0	-	μA	

Specifications DG411/883, DG412/883, DG413/883

TABLE 2. AC ELECTRICAL PERFORMANCE CHARACTERISTICS

Device Tested at: $V_+ = +15V$, $V_- = -15V$, $V_L = 5V$, $GND = 0V$, Unless Otherwise Specified

PARAMETERS	SYMBOL	CONDITIONS	GROUP A SUBGROUP	TEMPERATURE	LIMITS		UNITS
					MIN	MAX	
Turn ON Time	t_{ON}	$C_L = 35pF$, $V_S = \pm 10V$, $R_L = 300\Omega$	9, 11	+25°C, -55°C	0	175	ns
			10	+125°C	0	240	ns
		$V_+ = 12V$, $V_- = 0V$, $C_L = 35pF$, $V_S = +8V$, $R_L = 300\Omega$	9, 11	+25°C, -55°C	0	250	ns
			10	+125°C	0	400	ns
Turn OFF Time	t_{OFF}	$C_L = 35pF$, $V_S = \pm 10V$, $R_L = 300\Omega$	9, 11	+25°C, -55°C	0	145	ns
			10	+125°C	0	160	ns
		$V_+ = 12V$, $V_- = 0V$, $C_L = 35pF$, $V_S = +8V$, $R_L = 300\Omega$	9, 11	+25°C, -55°C	0	125	ns
			10	+125°C	0	140	ns

TABLE 3. ELECTRICAL PERFORMANCE CHARACTERISTICS (NOTE 1)

Device Tested at: $V_+ = +15V$, $V_- = -15V$, $V_L = 5V$, $GND = 0V$, Unless Otherwise Specified

PARAMETERS	SYMBOL	CONDITIONS	GROUP A SUBGROUP	TEMPERATURE	LIMITS		UNITS
					MIN	MAX	
Charge Injection	Q	See Figure 2, $V_G = 0V$, $R_G = 0\Omega$, $T_A = +25^\circ C$, $C_L = 10nF$	9	+25°C	-100	+100	pC
				+25°C			pC
		See Figure 2, $V_G = 6V$, $R_G = 0\Omega$, $T_A = +25^\circ C$ $C_L = 10nF$, $V_+ = 12V$, $V_- = 0V$	9	+25°C	-100	+100	pC
				+25°C			pC

NOTES:

1. V_{IN} = Input Voltage to Perform Proper Function.
2. Signals on S_X , D_X or IN_X exceeding V_+ or V_- will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
3. All leads soldered or welded to PC board.
4. Parameters listed in Table 3 are controlled via design or process and are not directly tested at final production. These parameters are lab characterized upon initial design release or upon design changes. These parameters are guaranteed by characterization based upon data from multiple production runs which reflect lot to lot and within lot variation.

TABLE 4. ELECTRICAL TEST REQUIREMENTS

MIL-STD-883 TEST REQUIREMENTS	SUBGROUPS (SEE TABLES 1 AND 2)
Interim Electrical Parameters (Pre Burn-In)	1
Final Electrical Test Parameters	1 (Note 1), 2, 3, 9, 10, 11
Group A Test Requirements	1, 2, 3, 9, 10, 11
Groups C and D Endpoints	1

NOTE:

1. PDA applies to Subgroup 1 only.

Die Characteristics

DIE DIMENSIONS:

2760 μ m x 1780 μ m x 485 $\pm$ 25 μ m

METALLIZATION:

Type: SiAl

Thickness: 12k $\text{\AA}$ $\pm$ 1k $\text{\AA}$

GLASSIVATION:

Type: Nitride

Thickness: 8k $\text{\AA}$ $\pm$ 1k $\text{\AA}$

WORST CASE CURRENT DENSITY:

1.5 x 10⁵ A/cm²

Metallization Mask Layout

DG411/883, DG412/883, DG413/883

